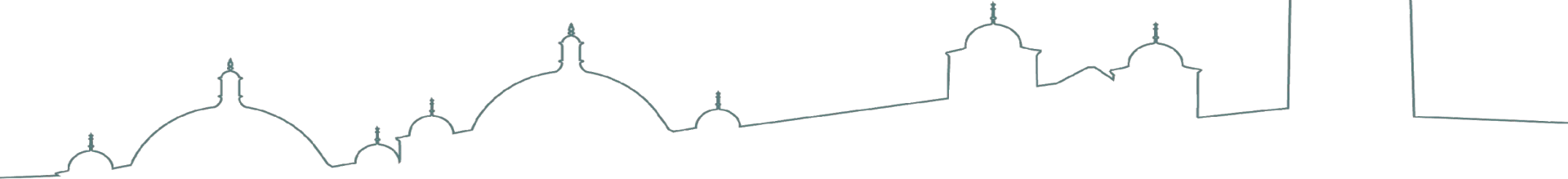


Cleaning of SNOGLOBE

Patrick Knights

University of Birmingham, UK, and IRFU, CEA Saclay, France



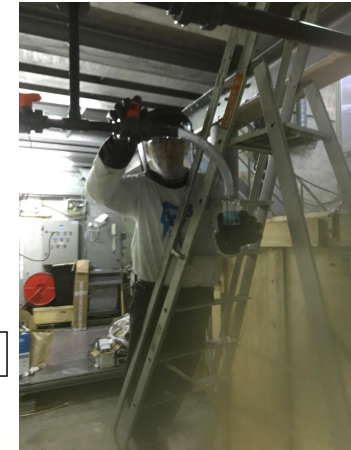
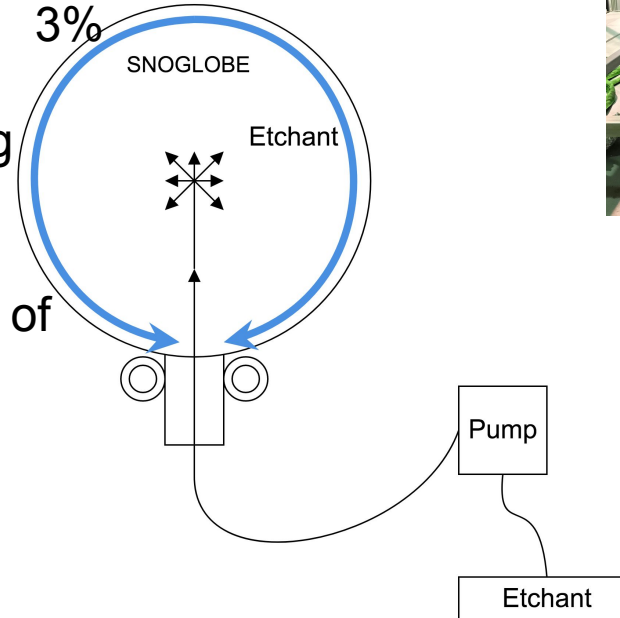
Internal Cleaning After Welding

- ⦿ During welding and pressure testing, inner surface was exposed to air and water
- ⦿ Cannot be certain how the sphere was handled by company
- ⦿ Decided on internal cleaning effort to suppress surface contamination
 - Etching and passivation



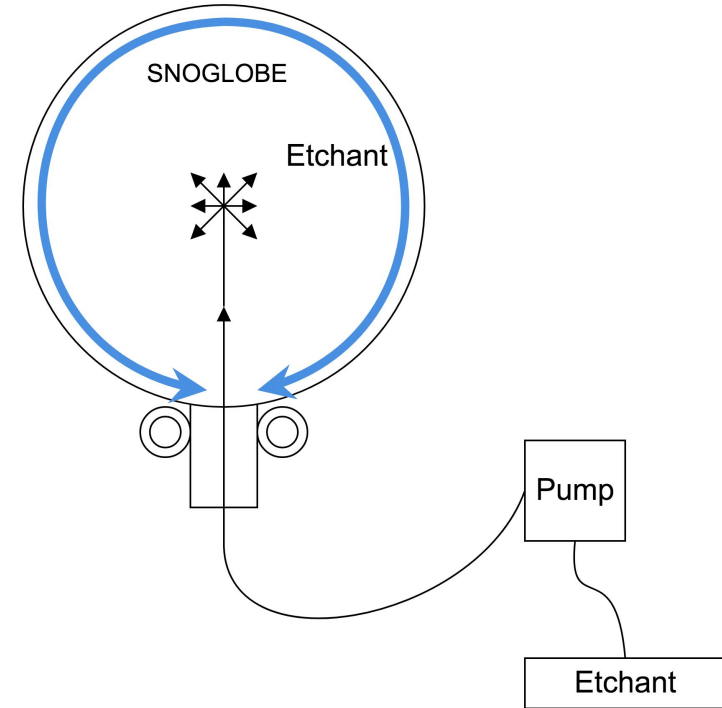
Etching of Internal Surface

- ⊙ Cleaned by chemical etching using 3% H_2O_2 , 1% H_2SO_4 in water
- ⊙ Samples of etchant collected during operation
 - ☐ Spectrophotometer used to measure copper concentration of etchant
 - ☐ ~2 μm of copper was removed
 - ☐ Etching took ~5.5 minutes



Internal Cleaning After Welding

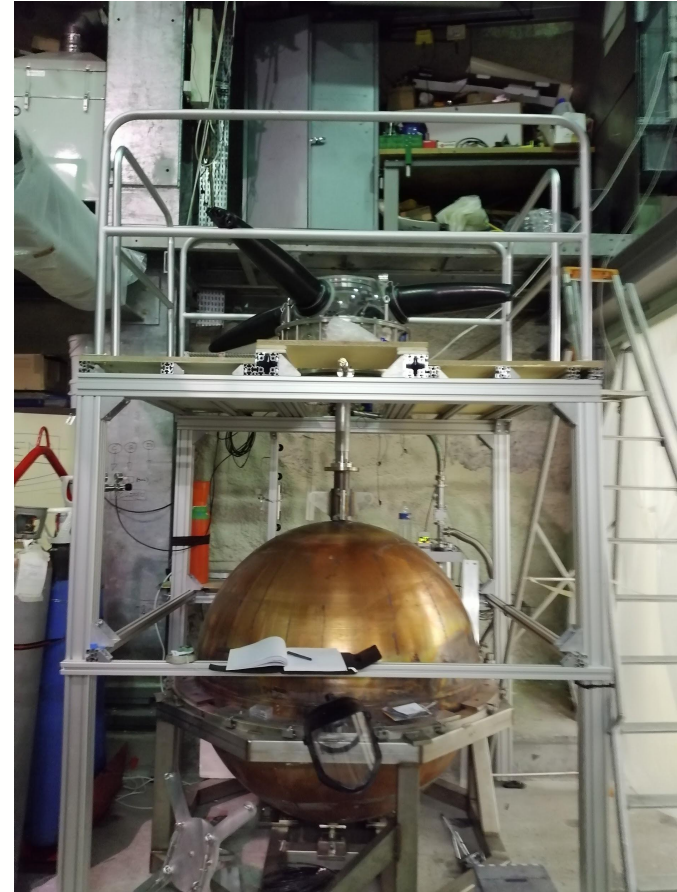
- ⦿ After rinsing, surface was passivated using 1% citric acid solution
- ⦿ Volume was flushed with nitrogen
 - ▣ Sphere was sealed and vacuum pumped after operation to minimise further contamination
- ⦿ Sphere has remained sealed since
 - ▣ Either in vacuum, nitrogen overpressure or filled with operating gas



Current State of External Surface

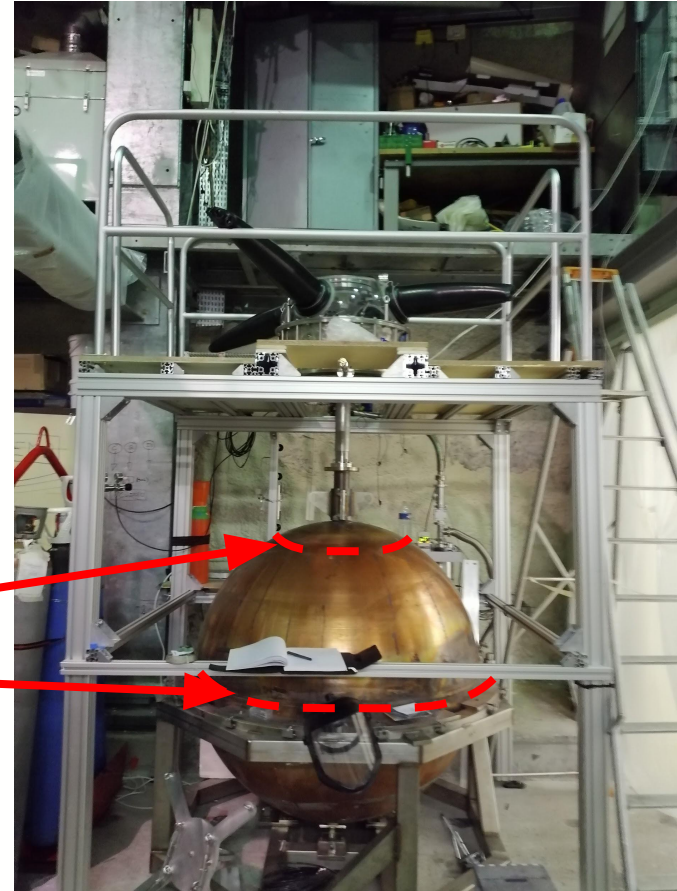
- ⦿ External surface needs to be cleaned in LSM for two main reasons
 - Contribution to background
 - Risk of contamination of the inner surface of the shielding

- ⦿ External surface has **several points for concern**
 - Copper deposited on the outside
 - Rough parts of copper, trapping dirt
 - Burnt stickers/tape
 - Tape and adhesive from tape



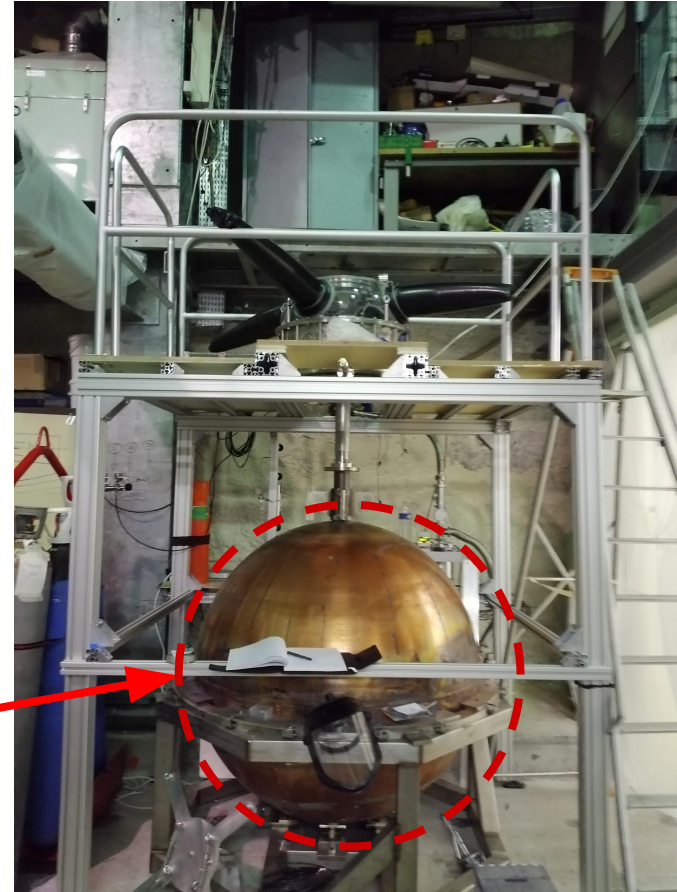
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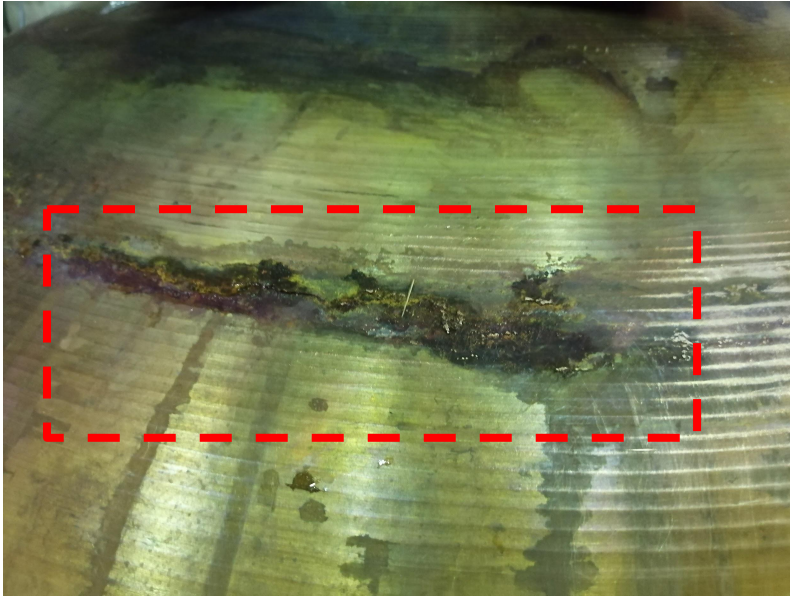
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 - Risk of contamination of the inner surface of the shielding
- External surface has **several points for concern**
 - Copper deposited on the outside
 - Rough parts of copper, trapping dirt
 - Burnt stickers/tape**
 - Tape and adhesive from tape**



Extra Copper Deposited on Outside

- ⊙ Deposited due to leak of electrolyte during cleaning
- ⊙ Extra copper is not a problem, but the trapped dirt is



- ⊙ **Solution:** Sand away enough copper to allow surface to be cleaned



Rough Copper Surface at Equator

- ⊙ Due to electrolyte leak, copper removed in 'groves' at equator
 - Only a problem if it is trapping dirt
- ⊙ **Solution:** Clean well with hard-bristled brush and Micro90 (detergent). Ensure etchant gets into groves. Perhaps sand particularly rough parts

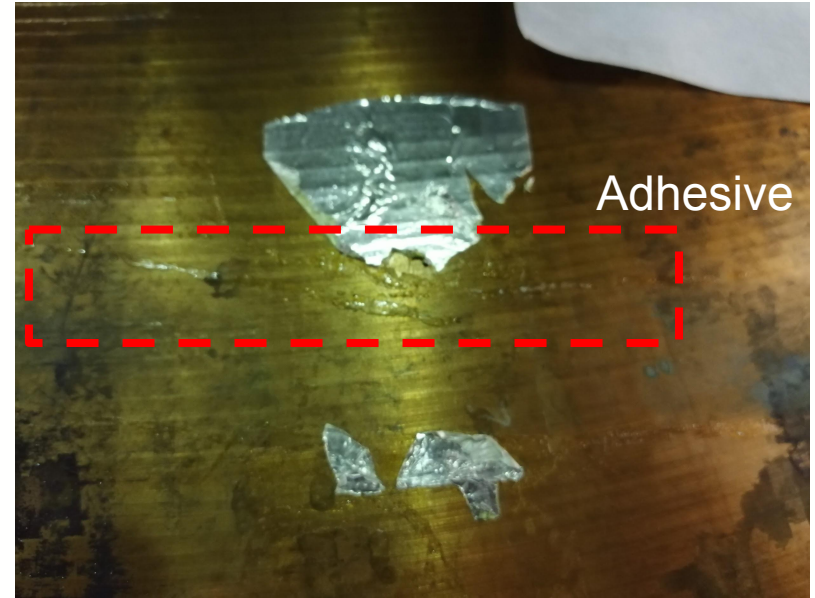


Burned Stickers/Tape

- ⦿ Looks like tape was burned to the outside of the sphere
 - Probably during welding or in baking
- ⦿ **Solution:** Sanding. I wasn't able to remove it with alcohol or acetone



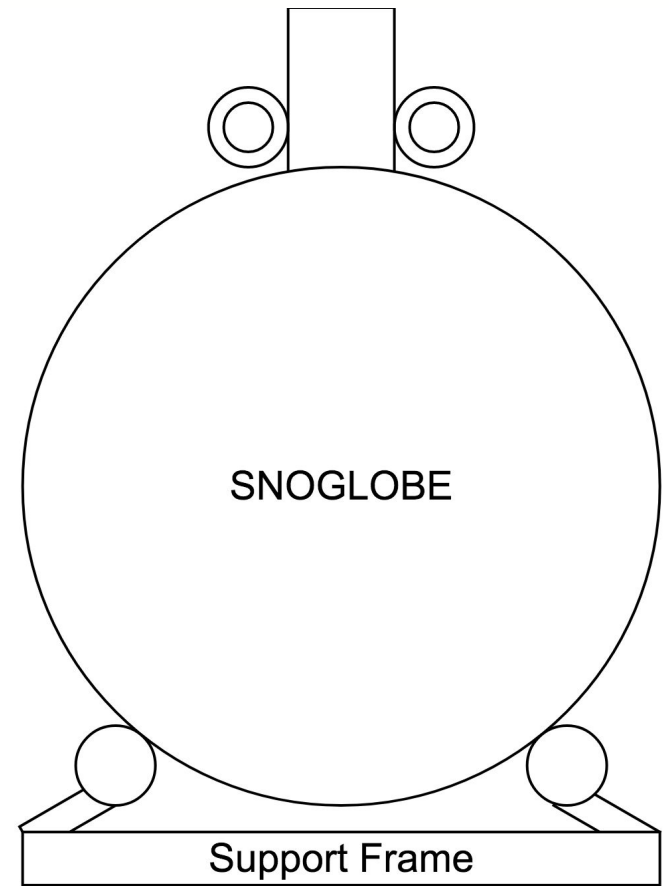
Tape and Adhesive from Tape



- Tape that could not be removed by hand. Also left some adhesive
- Tried to clean with alcohol and acetone, but not successful
- **Solution:** With hard scrubbing they will come off, or Eric Hoppe recommended MEK (methyl ethyl ketone) or MIBK (methyl isobutyl ketone) solvents

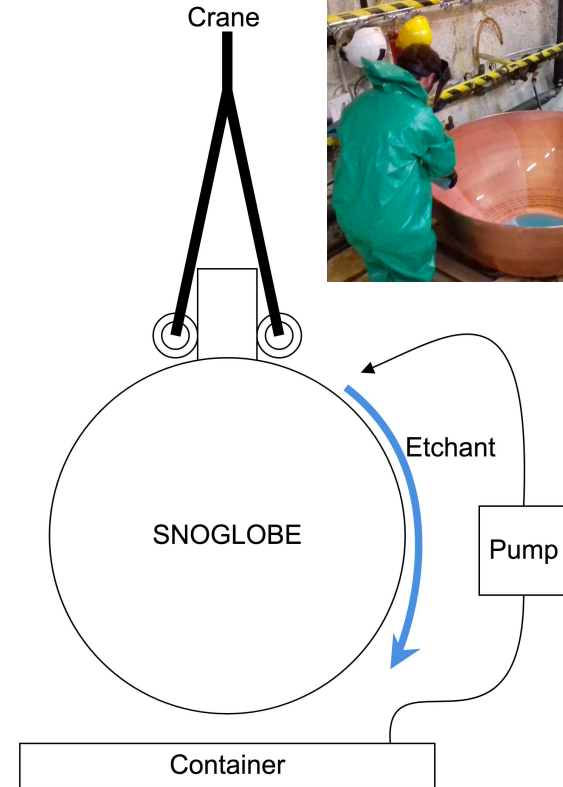
Cleaning Procedure - Sanding

- ⦿ Sphere will be moved to entrance of lab
 - ☐ Too much dust produced to do sanding in sphere's current location
- ⦿ Sanding should be completed before other cleaning
 - ☐ Should be done with fine-grit silicon carbide paper where possible
- ⦿ Should also clean the tape/adhesive residue at this stage with solvent or scrubbing

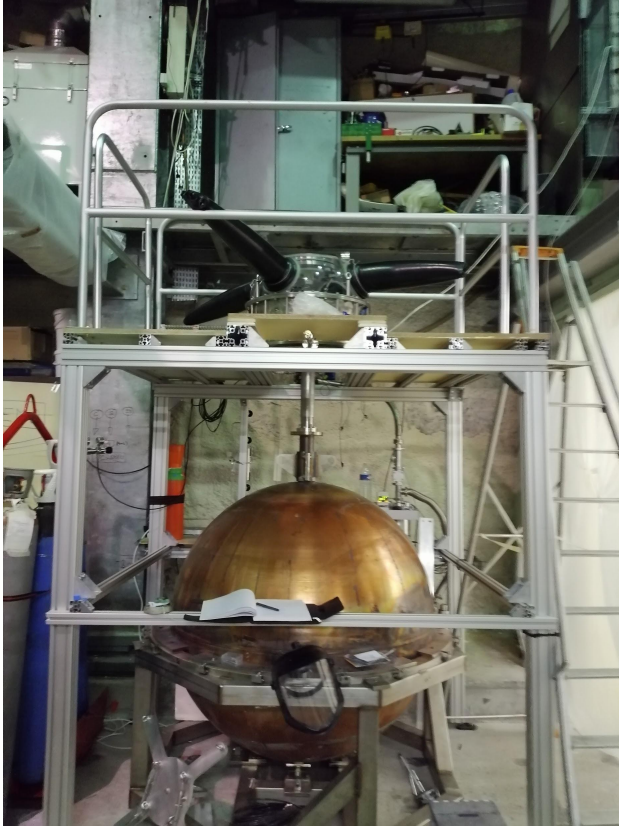


Cleaning Procedure - Detergent and Etching

- ⦿ Surface should then be washed with Micro90 detergent (1%) in water (balance)
 - ▣ Use hard bristle brush to remove all trapped dirt/oil
- ⦿ Rinse
- ⦿ Chemically etch surface with 3% H_2O_2 , 1% H_2SO_4 in deionised/demineralised water
 - ▣ Pump will be used to circulate the etchant
- ⦿ Should be rinsed afterwards
- ⦿ Passivate surface with 1% Citric acid solution



Summary



- ◎ Internal surface was chemically etched and passivated following the welding
 - ❑ Not exposed to air since (and won't be ever again!)

- ◎ External surface require some attention
 - ❑ Several points of concern for cleanliness

- ◎ Operation to perform the external cleaning will take place next week
 - ❑ All required materials are available in LSM

- ◎ Full procedures are available on the TWiki:
<https://www.snolab.ca/news-projects/private/TWiki/bin/view/Main/DetectorSurface>

Additional Material

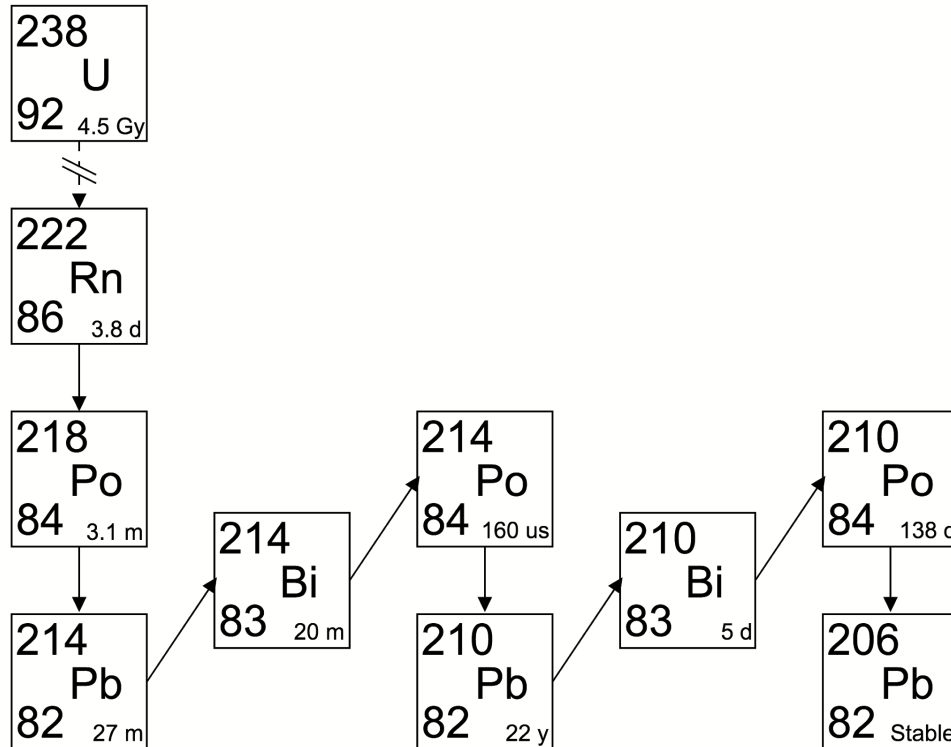
Copper as a Construction Material

- ◎ **Copper** is common material of choice for such experiments:
 - ❑ Strong enough to build limited-pressure vessels or support structures
 - ❑ Commercially available at high purity
 - ❑ Low cost
 - ❑ **No long-lived radio-isotopes**
 - Longest is ^{67}Cu , $t_{1/2} = 62$ hours
 - ❑ Possibility to **electrochemically purify**



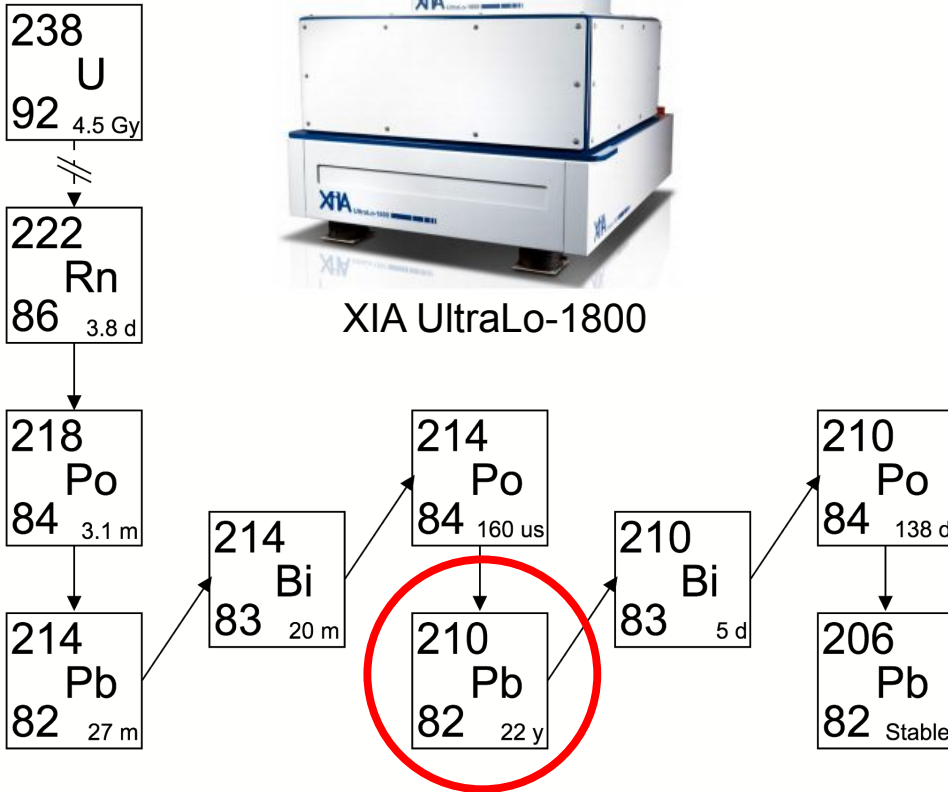
SEDINE,
DM Detector
(NEWS-G)

Background Contributions in Copper



- ⊙ $^{63}\text{Cu}(n,\alpha)^{60}\text{Co}$ by fast neutrons from cosmic muon spallation
- ⊙ ^{238}U and ^{232}Th decay chain – traces naturally found and deposited by ^{222}Rn
- ⊙ ^{238}U and ^{232}Th contamination:
 - Commercial copper $\sim 1\text{-}10 \mu\text{Bq/kg}$

^{210}Pb Measurements



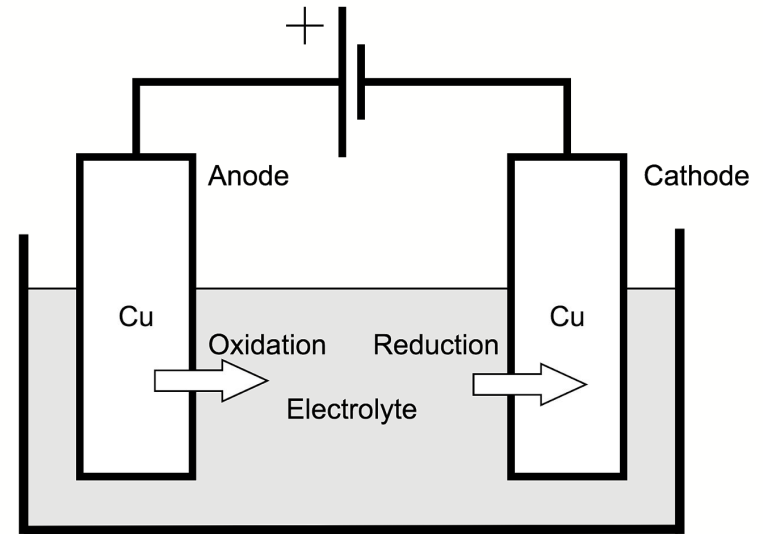
- ⊙ ^{238}U content **measured directly** by mass spectroscopy
 - ▣ **Used to infer daughter isotopes'** quantities in material
- ⊙ But ^{222}Rn deposits daughter nuclei on surfaces during production, mixing into bulk copper
 - ▣ ^{210}Pb has a 22-year half-life – **amount may be larger than that inferred from ^{238}U**
- ⊙ Recent method to measure ^{210}Pb from ^{210}Po α -decays

See XMASS collaboration: doi.org/10.1063/1.5018989
<https://www.xia.com/ultral0-theory.html>

Electrolytic Cell and Electroplating

- ⊙ **Electrolysis** governed by **oxidation** and **reduction** reactions
- ⊙ Reduction of ions requires supply of electrons → **Current**
- ⊙ Also requires energy → **potential difference**
- ⊙ **Ions reduced at cathode**: material build-up
 - ▣ Supplied current drives reaction
 - ▣ Deposited mass proportional to current:

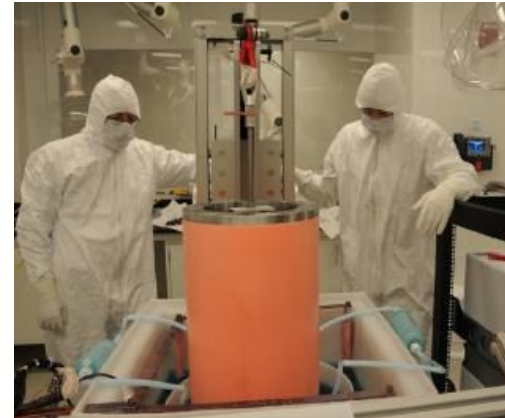
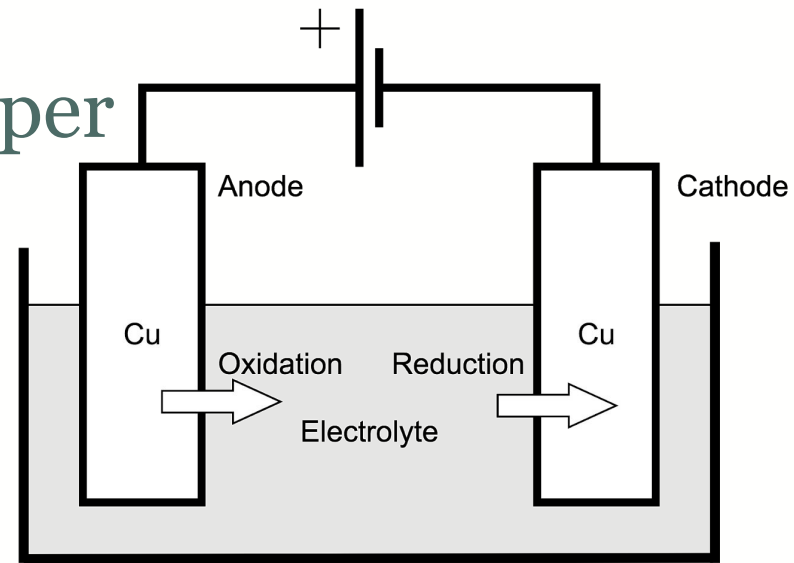
$$M = \frac{m_r \int I(t) dt}{zF}$$



M - mass deposited
 m_r - molar mass
 $I(t)$ - current
 z - number of electrons transferred
 F - Faraday Constant(= eN_A)

Electroplating Ultra-Pure Copper

- Some ions reduce more readily than others → **reduction potentials**
- Copper benefits from '**electrowinning**' - high reduction potential +0.34 V
- Reduction potential of:
 - Uranium (U^{3+}): -1.80 V
 - Thorium (Th^{4+}): -1.90 V
 - Lead (Pb^{2+}): -0.13 V
- Lower than copper → **copper refined during electroplating** if electrode potential is low enough



Example:
Electroforming at
PNNL

<https://www.pnnl.gov/science/highlights/highlight.asp?id=1434>

Why don't impurities plate too?

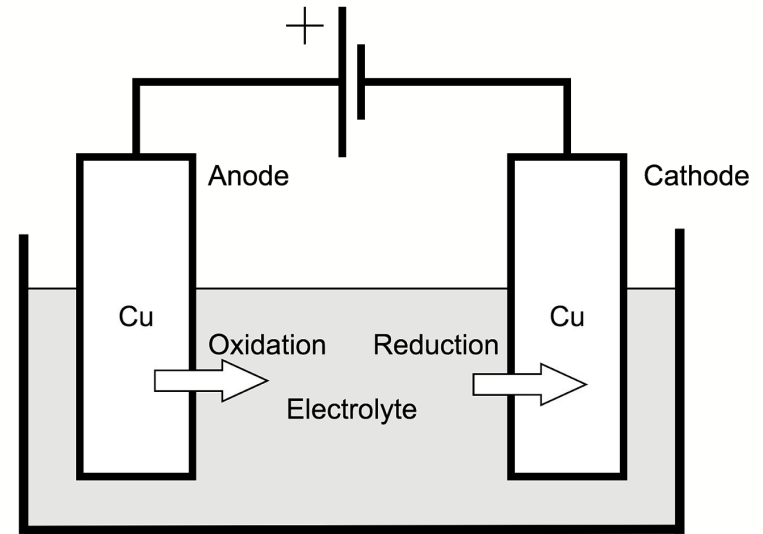
- Reaction that proceeds determined by standard cell potential:

$$E_{cell}^0 = E_C^0 - E_A^0$$

- Related to change in Gibbs Free Energy:

$$\Delta G^0 = -zFE_{cell}^0$$

- If $\Delta G^0 < 0$, then reaction is spontaneous
- If $\Delta G^0 > 0$, then extra energy is needed



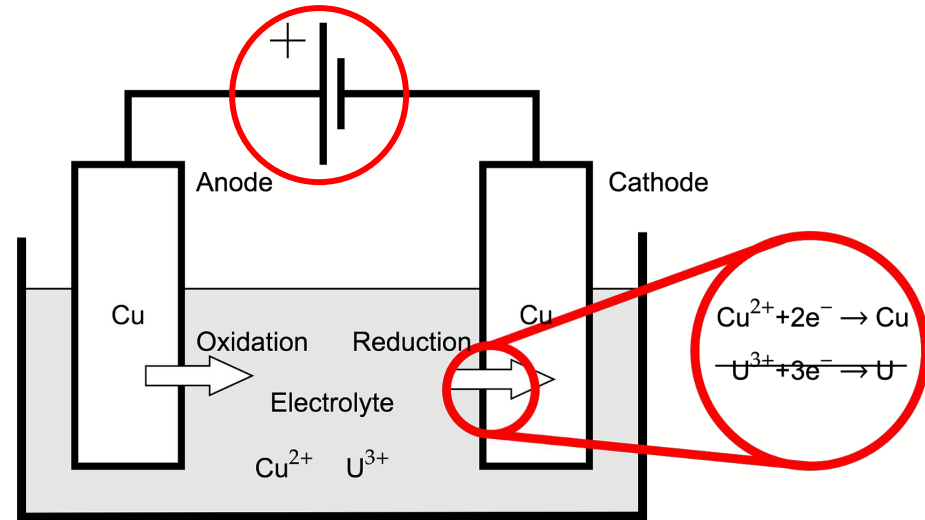
E_{cell}^0 - standard cell potential

E_C^0 - standard reduction potential at cathode

E_A^0 - standard reduction potential at anode

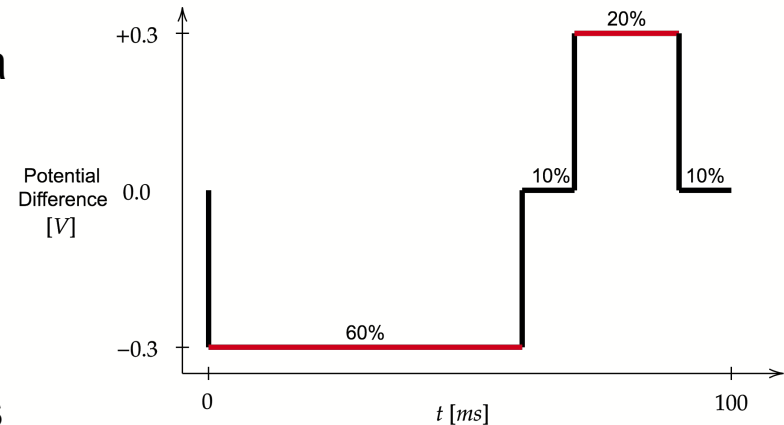
An Example: Uranium Contamination

- Example of **electrolyte containing U^{3+} and Cu^{2+} ions**, with a Cu anode:
- To reduce U^{3+} to U
 - $E_{cell}^0 = -2.14 \text{ V} \rightarrow$ Requires energy
- To reduce Cu^{2+} to Cu
 - $E_{cell}^0 = 0 \text{ V} \rightarrow$ In **equilibrium**
- Cu^{2+} reduction is energetically favourable to U^{3+} reduction
- Potential difference required to drive reaction and overcome energy losses



Pulse Plating for better characteristics

- ⊙ Voltage application: DC or pulsed
- ⊙ **'Pulse plating'** or 'pulse-reverse plating' uses waveform for electroplating
 - ☐ Relaxation period and sometimes with a 'polishing' section
- ⊙ Demonstrated benefits over DC plating:
 - ☐ **Raised areas reduced** by reverse bias section of pulse
 - ☐ **Greater uniformity of deposit** – relaxation period allows diffusion of ions
 - ☐ **Higher density deposit**



Radiopurity Results for Electroformed Copper

Copper Type	^{232}Th [ppt] ($\mu\text{Bq/kg}$)	^{238}U [ppt] ($\mu\text{Bq/kg}$)	Source
C10100	0.46±0.06 (1.19±0.25)	0.21±0.06 (2.54±0.74)	Majorana Demonstrator, (PNNL) 10.1016/j.nima.2016.04.070
Electroformed	<0.029 (<0.11)	<0.008 (<0.10)	Majorana Demonstrator, (PNNL) 10.1016/j.nima.2016.04.070
Electroformed	0.035±0.004 (0.14)	<0.050 (<0.06)	CES, LSC 10.1063/1.5018987

- ◎ Current ^{238}U and ^{232}Th contaminations below sensitivity of most sensitive assay technique - ICP-MS
 - Bounds are just upper limit – value may be much lower

^{210}Pb in Electroformed Copper

- Electroformed copper shows factor ~5 or more reduction in ^{210}Pb compared to Oxygen free copper (OFC)
 - Inferred from measurements of ^{210}Po α -particles
- Measurements of electroformed copper were limited by background

See XMASS collaboration: doi.org/10.1063/1.5018989

Sample	^{210}Pb contamination (mBq/kg)	^{210}Po contamination (mBq/kg)
OFC#1 (C1020) (MMC)	40±8	47±21
OFC#2 (C1020) (MMC)	20±6	33±14
OFC#3 (C1020) (MMC)	27±7	(1.6±0.3)×10 ²
OFC#4 (C1020) (MMC)	23±8	(2.2±0.4)×10 ²
OFC#5 (C1020) (SH copper products)	17±6	44±18
OFC#6 (C1020) (SH copper products)	27±8	24±17
OFC (class1) (SH copper products)	36±13	38±3
Coarse copper (MMC)	(57±1)×10 ⁻³	(16±2)×10 ⁻³
Bare copper (MMC)	8.4±4.0	(1.1±0.2)×10 ²
OFC (MMC)	23±8	(1.3±0.3)×10 ²
6N copper (MMC)	<4.1	<4.8
Electroformed copper (Asahi-Kinzoku)	<5.3	<18

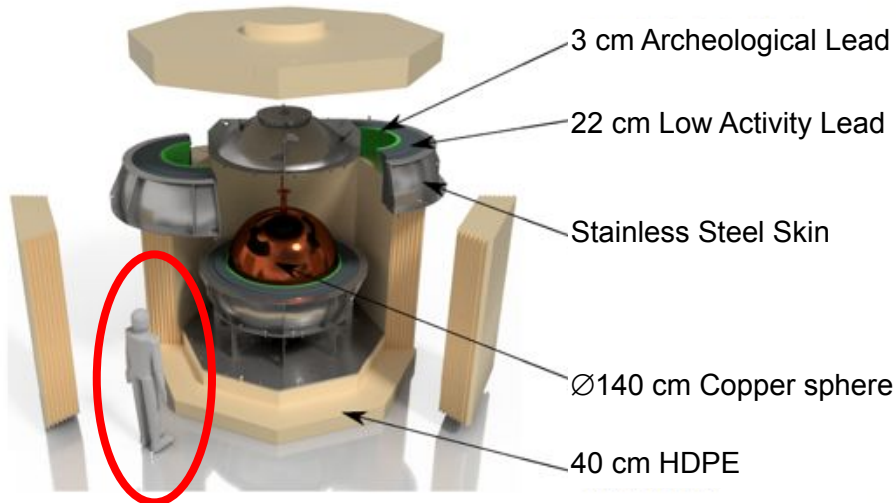


XIA UltraLo-1800

<https://www.xia.com/ultral0-theory.html>

NEWS-G - Next Generation

- ⦿ Next NEWS-G detector is a $\varnothing 140$ cm Cu sphere
 - Aurubis C10100 4N (99.99% pure) copper
- ⦿ To be installed in LSM, Spring/Summer 2019 for first tests
- ⦿ Shipped to SNOLAB, Autumn 2019



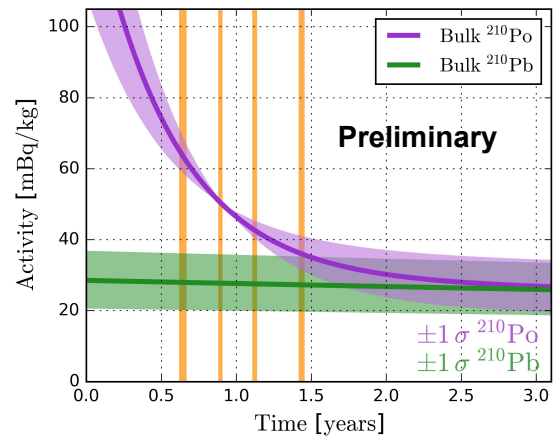
Test of hemisphere spinning

^{210}Pb in NEWS-G Copper

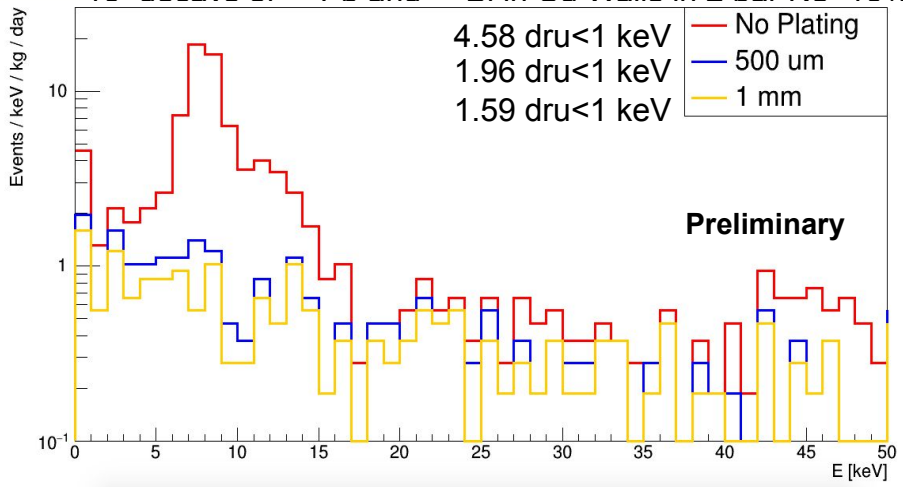
- Collaborative agreement between XMASS and NEWS-G to perform four measurements of ^{210}Po , every three months
- Preliminary analysis indicates ^{210}Pb at 28.5 ± 8 mBq/kg
 - Similar to other samples
- Geant4 simulation indicated that this gives **4.58 dru* < 1 keV**
- Reduced to 1.96 dru if 0.5 mm of pure copper is electroplated onto the inner surface
 - Other sources ~ 0.6 dru

*1 dru = 1 count/keV/kg/day

Best Estimate of ^{210}Po & ^{210}Pb from two measurements of ^{210}Po

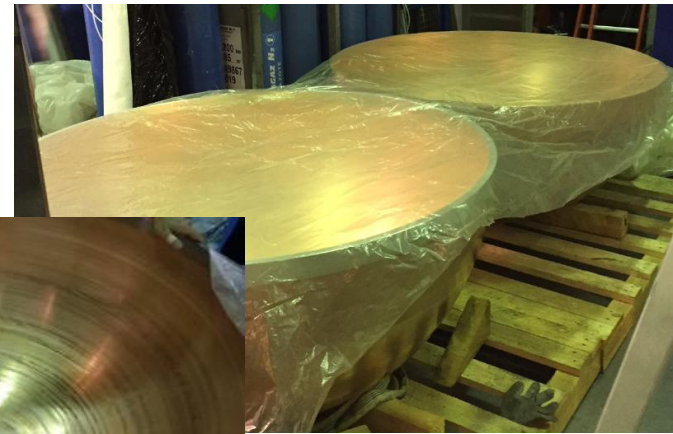


10^7 decays of ^{210}Pb and ^{210}Bi in Cu Walls in 2 bar Ne+10% CH_4



Preparation of Surface

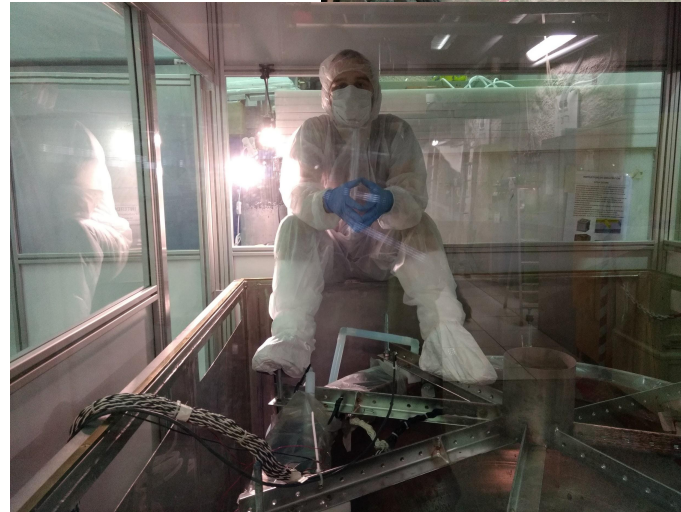
- ⊙ Operation performed in **LSM**
- ⊙ Sanded to remove rough parts
- ⊙ Cleaned surface with **Micro90 detergent**
- ⊙ Chemically etched using 3% H_2O_2 , 2% H_2SO_4 in deionised water
 - ☐ Shown to be effective etchant while less aggressive than alternatives such as nitric acid
- ⊙ Same treatments for **copper anode**



More on surface preparation: <https://doi.org/10.1016/j.nima.2007.04.101>

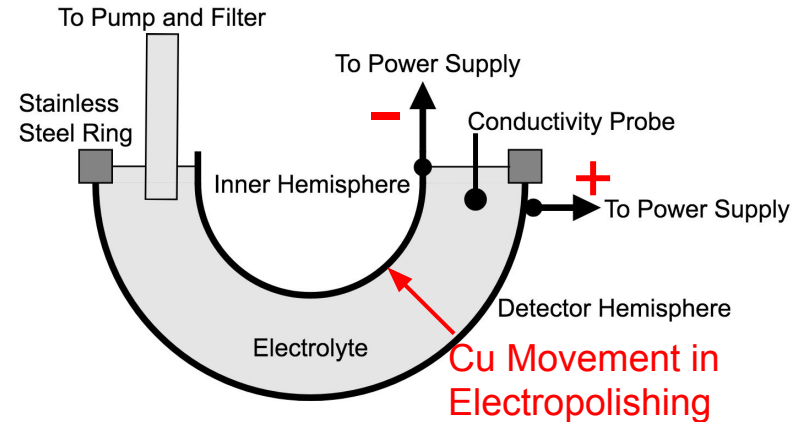
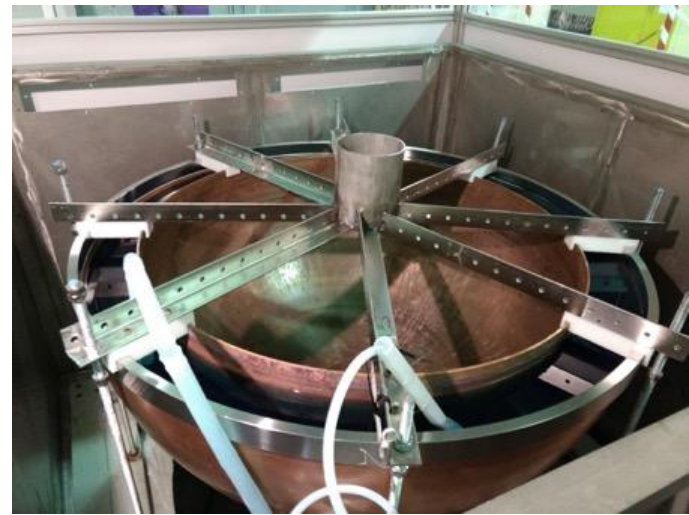
Installation for Electroplating

- ⦿ Hemisphere moved to enclosed **clean area** where electroplating was carried out
- ⦿ Electrolyte of H_2SO_4 , H_2O and CuSO_4
- ⦿ Pump and 1 μm particulate filter installed
 - ▣ Provides mechanical mixing and filtration
- ⦿ Anode installed into hemisphere, separated by 12 cm



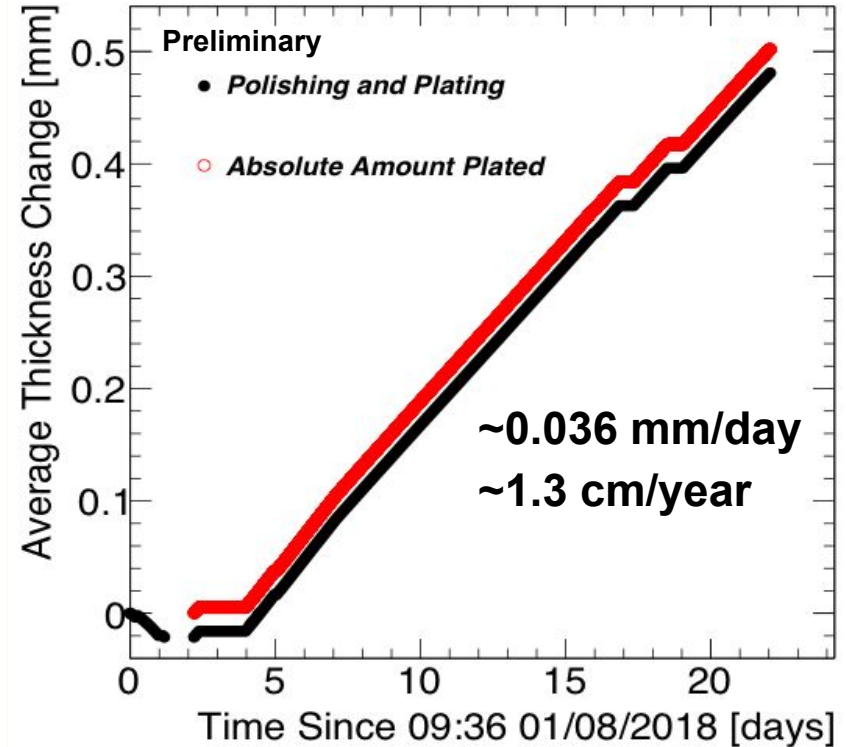
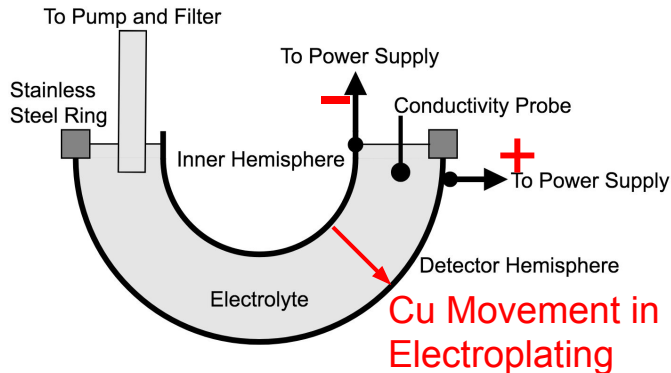
Electropolishing

- Electropolishing serves several purposes
 - Removes layer without chemical or mechanical attack
 - Preferentially removes raised areas on surface
 - Increases concentration of CuSO_4 in electrolyte**
- Pulse plating** used
- Estimated first (second) hemisphere $21\ \mu\text{m}$ ($28\ \mu\text{m}$) polished, based on current measurements

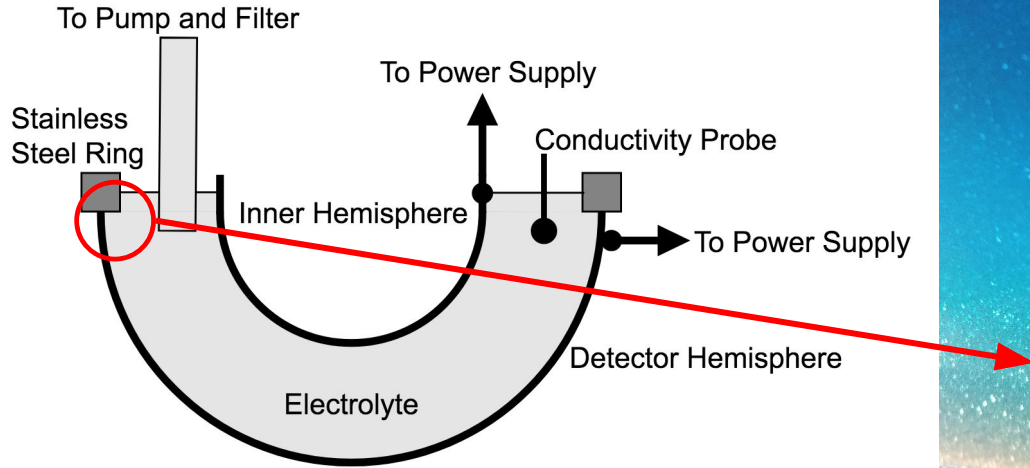


Electroplating

- ⊙ Electrode potential difference of **~ 0.3 V used**
 - ☐ Established value for copper
- ⊙ Plating continued for ~ 15 days
- ⊙ In total estimate first (second) hemisphere had **$502 \mu\text{m}$ ($540 \mu\text{m}$)** plated, based on current measurements



Electroplating - Results



- ◎ Copper depositing on hemisphere surface

Electroplating Results



- ⦿ Layer of Cu deposited on surface
 - Awaiting results of analysis to verify purity
- ⦿ Rinsed and passivated with citric acid before hemispheres welded together
- ⦿ Final chemical etch performed on intact sphere
- ⦿ Detector being installed in LSM for first tests and commissioning

Cosmogenic Activation of Copper

- Produced by $^{63}\text{Cu}(n,\alpha)^{60}\text{Co}$ with fast neutrons from cosmic muon spallation
- ^{60}Co $t_{1/2} = 5.3$ years
- Saturation activity of ^{60}Co $340^{+82}_{-68} \mu\text{Bq/kg}^*$

*Baudis, L., Kish, A., Piastra, F. et al. *Eur. Phys. J. C* (2015) 75: 485. <https://doi.org/10.1140/epjc/s10052-015-3711-3>

Table 3 Results for the specific saturation activity A_{sat} of natural copper at sea level, derived from our measurements of the cosmogenic activation. These are compared to our predictions from Activia and Cosmo, using semi-empirical formulae for the cross sections

Isotope	$T_{1/2}$ [days]	Copper: specific saturation activity at sea level A_{sat} [$\mu\text{Bq/kg}$]								
		This work			Literature values					
		Measurement	Calculations		Measurement	Activia [12]		Calc. [44]		Calculation
			Activia	Cosmo		LNGS [42]	a	b	c	
^{46}Sc	83.79	27^{+11}_{-9}	36	17	25.2 ± 8.6	36	36	44	31	–
^{48}V	15.97	39^{+19}_{-15}	34	36	52 ± 19	–	–	–	–	–
^{54}Mn	312.12	154^{+35}_{-34}	166	156	394 ± 39	166	145	376	321	188
^{59}Fe	44.50	47^{+16}_{-14}	49	50	57 ± 14	49	21	75	57	–
^{56}Co	77.24	108^{+14}_{-16}	101	81	110 ± 14	101	163	153	231	–
^{57}Co	271.74	519^{+100}_{-95}	376	350	860 ± 190	376	421	1022	858	650
^{58}Co	70.86	798^{+62}_{-58}	656	632	786 ± 43	655	441	1840	1430	–
^{60}Co	1925.28	340^{+82}_{-68}	304	297	1000 ± 90	304	112	1130	641	537

Co^{2+} Reduction Potential = -0.28 V

Standard Conditions

- ⊙ Temperature of 298.15 K (25.0°C)
- ⊙ Each gaseous reagent has a partial pressure of 1 atm (rarely 100 kPa)
- ⊙ Effective concentration of 1 mol/L for each aqueous species